



The Synthesis and Optical Dispersions Parameters of Cadmium Doped Tin Oxide Thin Films by the Sol-Gel Method

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ABSTRACT

In this study, undoped and Cd-doped SnO thin movies with unique atomic contents (0, 2, 4, and 6%) have been synthesized by means of the sol-gel method. The modifications in the optoelectrical residences of the Cd doped samples had been investigated with the aid of UV-VIS-NIR spectroscopy. The impact of Cd doping at the optical parameters of the SnO films becomes investigated by means of spectrophotometric measurements. The optical constants (absorption index, k and refractive index, n) of the samples have been determined in the wavelength variety of 300-800 nm. The dispersion parameters have been determined consistent with the version of a single oscillator model and discussed. The optical band gaps of the samples were calculated using Tauc Equation. It became discovered that the E_g values of the samples increased from 3,57 eV to 3,6 eV as a function of Cd doping.

Due to the studies, it turned determined that Cd doping has considerable results on the optical residences of SnO movies and the fabricated samples may be used for transparent conductive electrodes, optoelectronic gadgets, and sensor fabrication.

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1. INTRODUCTION

Tin is the oldest steel known to man. From ancient instances to the modern, Tin has been increasingly more utilized in various fields inclusive of coatings, compounds, and alloys with high era. As an example, in optical and electrical programs, the conductive materials are opaque (light-tight), at the same time as the permeable substances are insulating. But, this isn't authentic for Tin Oxide (SnO₂). That is due to the fact Tin Oxide is permeable and conductive. The high permeability and semiconducting residences of SnO₂ permit it to maintain the conductivity and permeability residences together. SnO₂ is the most commonplace Tin compound. SnO₂ is an n-type semiconductor with a large band (3,6-3,8 eV) [1] and has high optical transmittance within the seen region. similarly, it has numerous precise residences together with low electrical conductivity, high reflectance for infrared light, excessive mechanical hardness, and chemical and thermal stability [2]. Due to these super residences, SnO₂ is extensively utilized in lithium-ion batteries, fuel sensors, sun batteries, optoelectronic devices, mild-emitting diodes, architectural glass, and aircraft glass [3].

The structural, physical, and chemical residences of SnO₂ can be advanced by way of doping with diverse transition metals, that is why the usage of those substances is progressively growing. Amongst all the transition metals,

Cd is one of the favored metals due to the fact it's far incredibly soluble in stable shape and is a stable compound within the variety of different Sn/Cd ratios [4]. Several scientific studies were executed on this fabric as SnO₂ based nanomaterials may be prepared by way of many different methods. Literature reports that SnO₂ based totally materials can be organized via Physical Vapor Deposition (PVD), Chemical Vapor Deposition (CVP), Sol-Gel, Hydrothermal Techniques, Co-precipitation, and Spray Pyrolysis [5]. in this examine, undoped and Cd-doped SnO₂ skinny movies had been synthesized by means of Sol-Gel Spin Coating technique the use of Tin and Cadmium Acetate. Then, the effect of the synthesis parameters and Cd doping on the optical residences of the synthesized skinny movies become investigated.

2. EXPERIMENTAL DETAILS

All chemicals were used in this study as purchased from Sigma Aldrich, maintaining their analytical purity. Starting materials in the preparation of solutions, Tin (II) Acetate (Sn(CH₃CO₂)₂), Cadmium Acetate Dihydrate (Cd(CH₃COO)₂·2H₂O) (≥98.0%), 2-metoxyethanol (CH₃OCH₂CH₂OH) (99.8%) and monoethanolamine (MEA) (≥98%) as doping source, solvent and stabilizer was used, respectively. The amount of substance was calculated so that the prepared solutions were 1 M, 10 ml.

The starting materials were added to the solvents in the scaled beaker by weighing. These obtained mixtures were mixed with a magnetic stirrer at room temperature and then mixed in an ultrasonic stirrer to ensure homogeneity. After these steps, it was stirred at 60°C for 2 hours with the help of a magnetic stirrer to obtain the gel form of the solution. Microscope glass was used as a substrate for the magnification of these gels. Growth as a thin film on glass substrates was performed at room conditions with the aid of a spin coating (30 seconds at 1000 rpm). The thin films

3. RESULTS AND DISCUSSION

coated on the substrate were placed on a pre-set heater at 150°C and allowed to dry for 10 minutes. As a final step, the obtained films were heat-treated in an air atmosphere at 600 °C for 1 hour with the help of an oven. Thin films for all doping rates were prepared under the same conditions.

Optical spectra used to determine the optical properties of the nano-electroceramics and calculate the band gap were recorded using a SHIMADZU UV-VIS-NIR 3600 spectrophotometer in the wavelength range of 300 to 800 nm at room temperature.

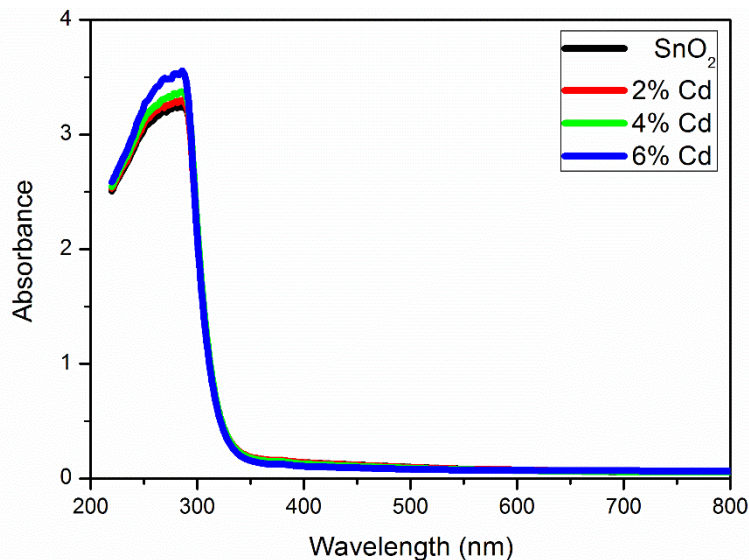


Figure 1: Absorbance spectra of undoped and Cd-doped Tin Oxide films

The absorption spectrum of the prepared thin movie samples is proven in Fig. 1. In Fig. 1, Cd-doped SnO skinny films display strong absorption traits at 300 nm and decrease wavelengths, and a non-stop growth in absorption

is found. this could be defined with the aid of the reality that photons are extra strongly absorbed at low wavelengths.

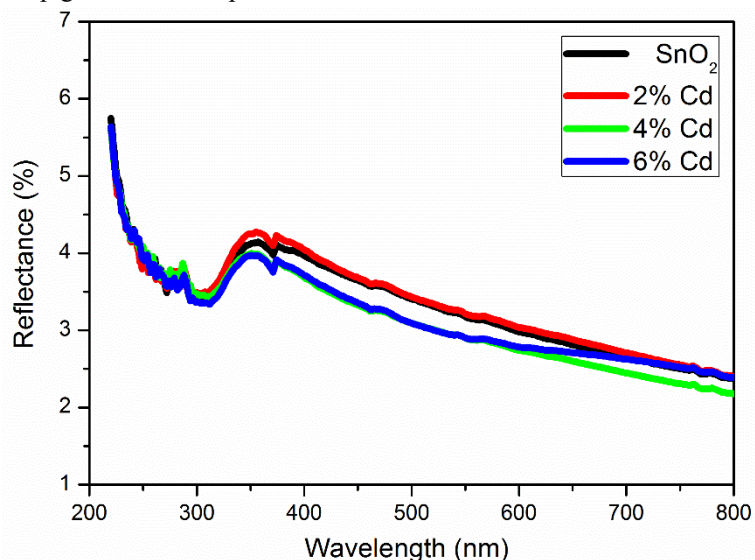


Figure 2: The reflectance spectra of the undoped and Cd-doped Tin Oxide thin films

The reflection spectra of the prepared thin film samples are given in Figure 2. As seen in Figure 2, the reflection curves of the samples have a peak in the wavelength range of 320-350 nm. This peak varies depending on the Cd ratio of the composition. This confirms that the optical band gaps of the films depend on the added Cd ratio. It can be said that the reflectance values obtained after the addition

of Cd are reduced compared to the undoped SnO sample. It is seen that the sample with the highest reflectance rate is the 2% Cd doped SnO sample. In addition, it is observed that the reflection values expand towards the short wavelengths. This is because, due to the increased energy of the photons, these photons are reflected as a result of

stronger interaction with electrons, atoms or crystal molecules.

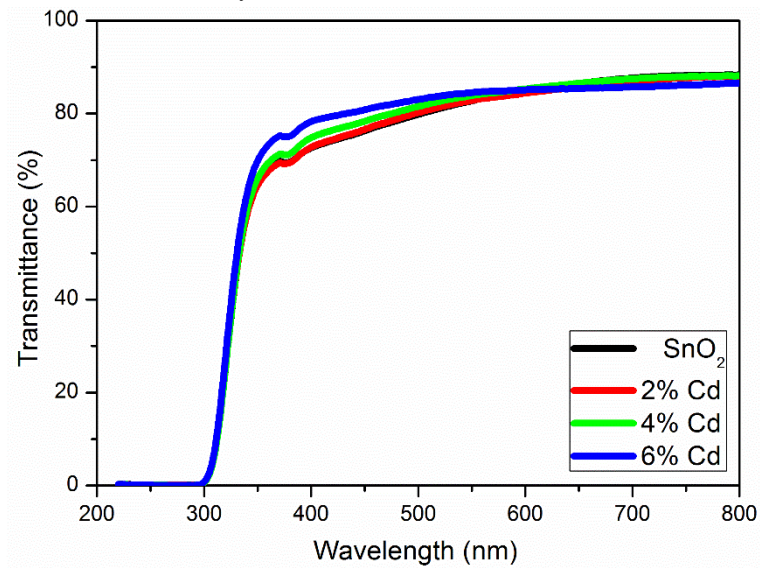


Figure 3: The transmittance spectra of the undoped and Cd-doped Tin Oxide thin films

The T spectra within the 300-800 nm slit of the evaluated modern-day samples are shown in Fig. 3. The prepared samples confirmed a transmittance of extra than 80% within the visible location. For all of the samples, the transparency value will increase with the growth of Cd doping compared to the undoped SnO sample. This boom is related to the structural houses of the movies, on the

grounds that changes in transmittance depend upon the cloth homes of the movies. in this admire, the fabricated samples are desirable obvious semiconductors. In Fig. 3, a pointy absorption band at wavelengths of 350 nm may be seen within the transmission spectrum of the skinny movies. This band facet decreases in parallel with the increasing Cd concentration.

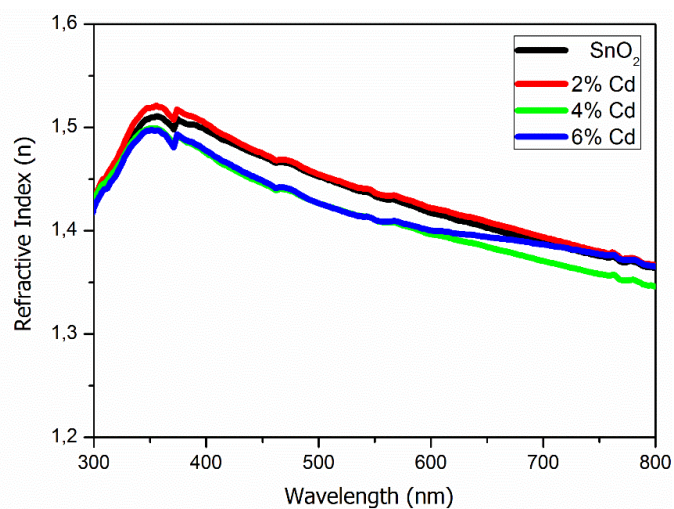


Figure 4: Refractive index (n) of undoped and Cd doped SnO films

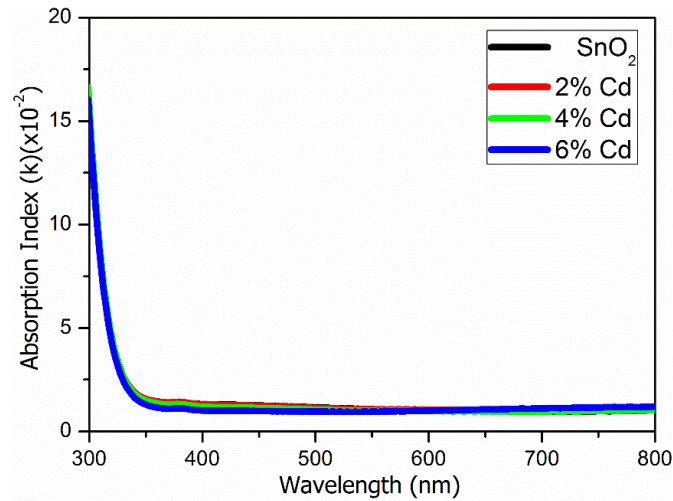


Figure 5: Absorption index (*k*) of undoped and Cd doped Tin oxide films

Determining the refractive index of semiconductor substances through exploiting the optical houses of the fabric performs a vital function in figuring out the suitable software region, tool design, and accurate modeling. The *n* and *k* values of the nanostructured skinny movies fabricated via sol-gel technique were decided the use of the permeability and reflectance spectra. The complicated refractive index of SnO-primarily based skinny films can be expressed with the aid of the subsequent relationship [6-9]:

$$\tilde{n} = n(\lambda) + ik(\lambda) \tag{1}$$

where *n* is the actual element and *k* is the imaginary a part of the complex refractive index. the usage of the reflectance values of the samples, the subsequent formula, referred to as the Fresnel formula, is used to calculate the refractive index (*n*).[10-13]:

$$n = \frac{(1+R)\sqrt{4R-(1-R)^2k^2}}{1-R} \tag{2}$$

The following formula can be used to obtain the damping coefficient (*k*) [14-16]:

$$k = \frac{\alpha\lambda}{4\pi} \tag{3}$$

Where, λ and α represent the wavelength and absorption coefficient, respectively. The change in the *n* and *k* values, calculated by the Fresnel formula, with the wavelength is shown in Fig. 4 and Fig. 5, respectively.

As may be seen in Fig.5, the refractive index value typically will increase with increasing wavelength and then decreases. The sample with the highest refractive index price is 2% Cd-doped SnO. The gradual decrease of *n* and *k* is because of the lower of optical dispersion on the

surface and optical losses due to the growth of service concentration and the lower of surface roughness because of the trade of chemical composition of the samples with doping.

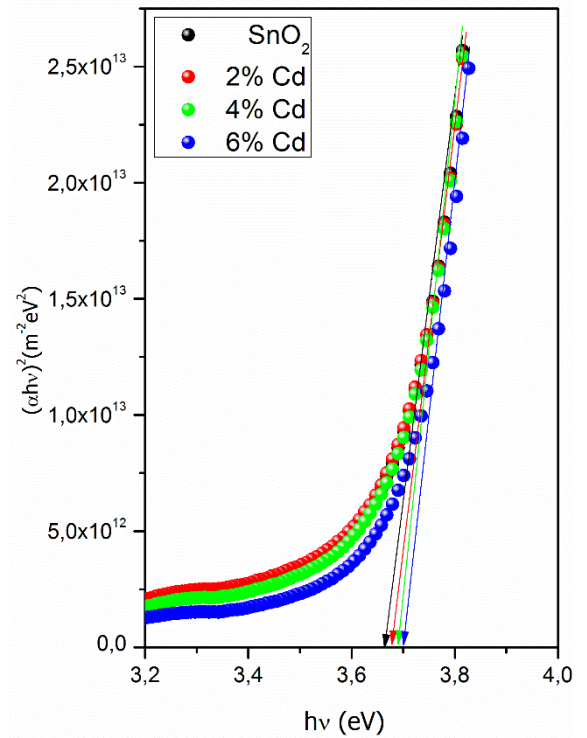


Figure 6: Plotting of $(\alpha hv)^2$ versus (hv) of undoped Cd doped SnO films

The optical band gap of the fabricated semiconductor skinny films was decided from the $(\alpha hv)^2-hv$ change diagram drawn the use of the basis absorption spectrum. The electricity price of the factor where the course of the linear a part of this transformation intersects the hv axis at $(\alpha hv)^2 = 0$ offers the optical band hole of the semiconductor. inside the calculation of the band hole, the method known as the Tauc equation is used[7, 17-19]:

$$(\alpha hv)^2 = A(hv - E_g) \tag{4}$$

Where in α is the absorption coefficient, hv is the photon energy, E_g is the optical band gap, and *A* is the constant.

The graphs of $(ahv)^2-hv$ organized to determine the optical band hole of undoped and Cd-doped nanostructured SnO movies are proven in Fig. 6. The optical band gaps (E_g) of the samples calculated the use of the curves in Fig. 6 had

been 3,67, 3,68, 3,69 and 3,70 eV for SnO and 2, 4 and 6% Cd, respectively. It's far observed that the sample with the bottom band hole is undoped SnO. The E_g of the samples generally expanded with growing Cd content.

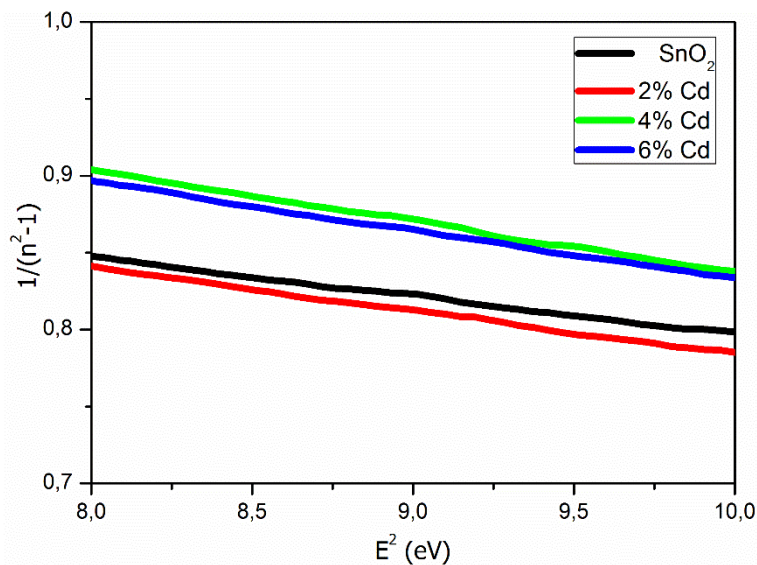


Figure 7: Plots of $(n^2-1)^{-1}$ versus $(hv)^2$ of undoped and Cd doped SnO films

Refractive dispersion performs an crucial function inside the observe of optical materials, being an critical thing within the layout of gadgets used for picture distribution in optical communications. The refractive index distribution

of the nanostructured thin films obtained in this take a look at become analyzed the use of the Wemple-Didomenico version (WD).

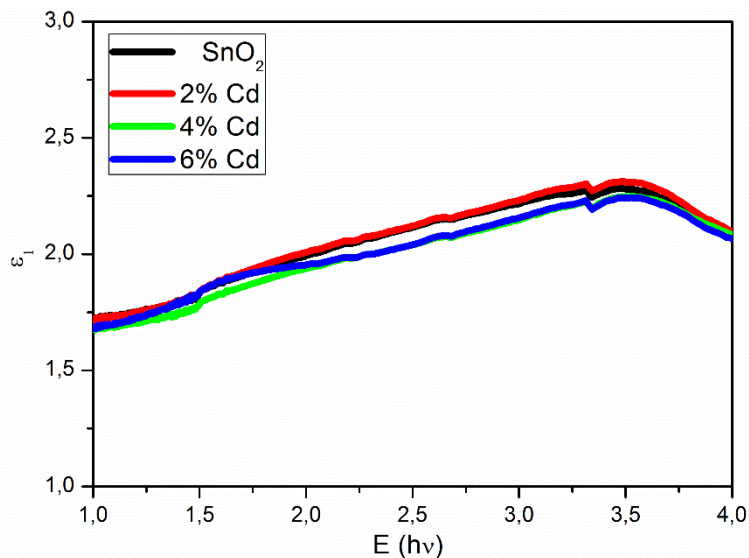


Figure 8: The variation of real parts of the dielectric constant of the undoped and Cd doped SnO thin films with photon energy

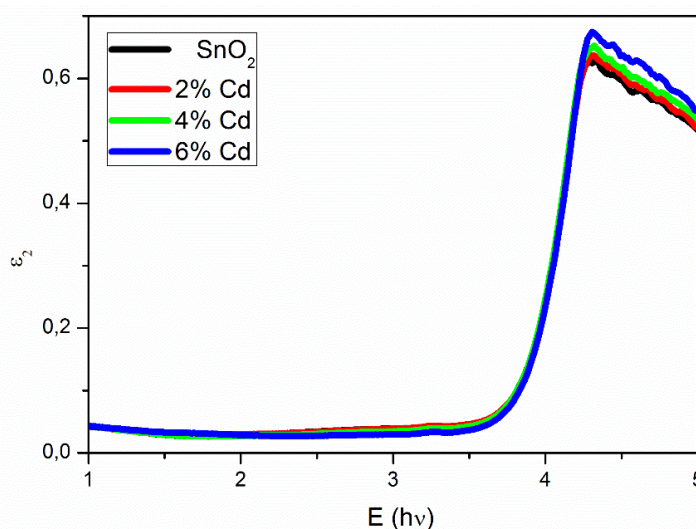


Figure 9: The variation of imaginary parts of the dielectric constant of the undoped and Cd doped SnO thin films with photon energy.

It is widely known that the polarizability of any stable cloth is proportional to the dielectric steady. That is related to the position density in the optical band hole. In this context, it's far crucial to observe the real and imaginary parts of the complicated dielectric steady. The dielectric regular is described as $\mathcal{E} = \mathcal{E}_1 + i\mathcal{E}_2$, in different phrases the actual and imaginary parts of the complex dielectric consistent. this example is expressed as follows [5, 11, 20, 21]:

$$\varepsilon_1 = n^2 - k^2 \quad (5)$$

And

$$\varepsilon_2 = 2nk \quad (6)$$

The dependence of the real (\mathcal{E}_1) and imaginary parts (\mathcal{E}_2) components of the dielectric steady at the photon power ($h\nu$) is proven in Fig.8 and Fig.9, respectively. By using looking at Fig.8 and Fig.9, it is found that the actual and digital dielectric regular adjustments for all nanostructured thin movies inside the visible location. The conductivity values of the samples boom with increasing electricity. it's far assumed that this increase in optical conductivity is due to the electrons inspired via the photon electricity. within the graph of \mathcal{E}_2 in Fig.9, there is a top price that reflects the general band structure. This height is due to the method of photoexcitation, wherein electrons are excited from the valence band to the conduction band. The optical conductivity of the movies has changed due to Cd doping.

4. CONCLUSIONS

Undoped and Cd-doped SnO skinny films had been grown on glass base plates the usage of the sol-gel spin coating approach. The effect of Cd awareness at the optical properties turned into investigated. It has been observed that the samples have a direct band transition and the band gap changes with the Al contribution, which may be attributed to the Burstein-Moss shift. The outcomes imply that the optical houses of the fabricated SnO thin films are enhanced through Cd doping. These superior materials can be considered as potential candidates for use in transparent conductive electrode applications, photovoltaic devices and optoelectronic devices.

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